

20V N-Channel Mosfet

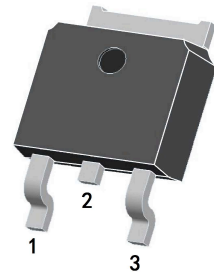
FEATURES

- $R_{DS(ON)} < 4m\Omega @ V_{GS} = 4.5V$
- $R_{DS(ON)} < 6m\Omega @ V_{GS} = 2.5V$

APPLICATIONS

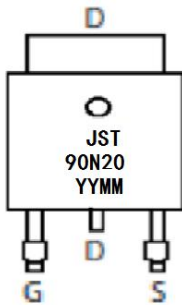
- Load Switch
- PWM Application
- Power management

TO-252

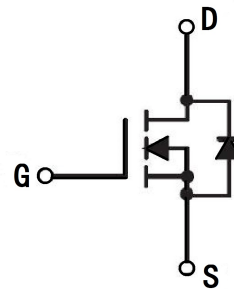


1: G
2: D
3: S

MARKING



N-CHANNEL MOSFET



YYMM:Date Code(year&month)

Maximum ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Max.	Units	
V_{DSS}	Drain-Source Voltage	20	V	
V_{GSS}	Gate-Source Voltage	± 12	V	
I_D	Continuous Drain Current	$T_C = 25^\circ C$	90	A
		$T_C = 100^\circ C$	59	A
I_{DM}	Pulsed Drain Current ^{note1}	360	A	
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	110	mJ	
P_D	Power Dissipation	$T_C = 25^\circ C$	81	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.85	$^\circ C/W$	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ C$	

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250μA	0.4	0.7	1.1	V
R _{DS(on)}	Static Drain-Source On-Resistance <small>note3</small>	V _{GS} = 4.5V, I _D = 30A	-	2.8	4	mΩ
		V _{GS} = 2.5V, I _D = 20A		4	6	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	-	3200	-	pF
C _{oss}	Output Capacitance		-	460	-	pF
C _{rss}	Reverse Transfer Capacitance		-	445	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D = 17A, V _{GS} = 4.5V	-	48	-	nC
Q _{gs}	Gate-Source Charge		-	3.6	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	19	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} = 15V, I _D = 17A, R _G = 1.8Ω, V _{GS} = 4.5V	-	9.7	-	ns
t _r	Turn-On Rise Time		-	37	-	ns
t _{d(off)}	Turn-Off Delay Time		-	63	-	ns
t _f	Turn-Off Fall Time		-	52	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 30A, T _J = 25°C	-	-	1.2	V
t _{rr}	Reverse Recovery Time	T _J = 25°C, I _F = 30A,	-	23	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs	-	10	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J = 25°C, V_{DD} = 15V, V_G = 4.5V, R_G = 25Ω, L = 0.5mH, I_{AS} = 21A

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%

Typical Characteristics

Figure 1: Output Characteristics

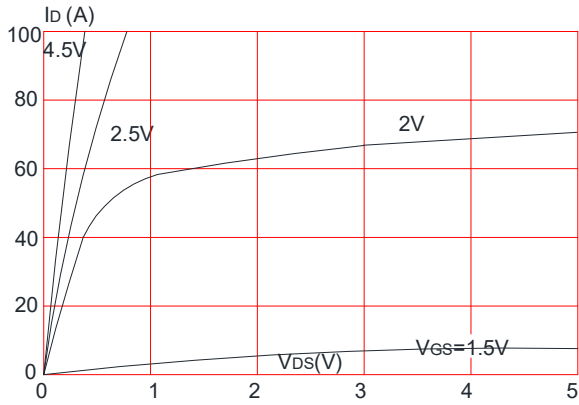


Figure 2: Typical Transfer Characteristics

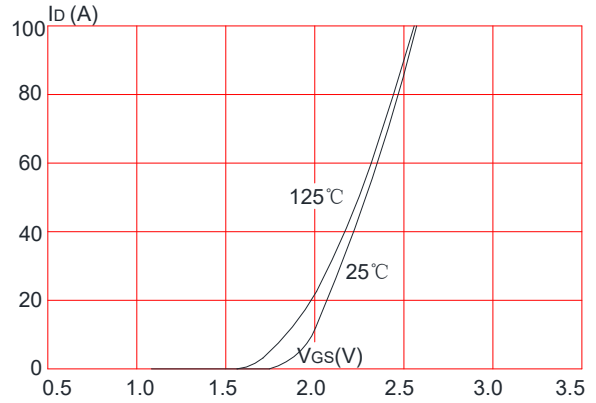


Figure 3: On-resistance vs. Drain Current

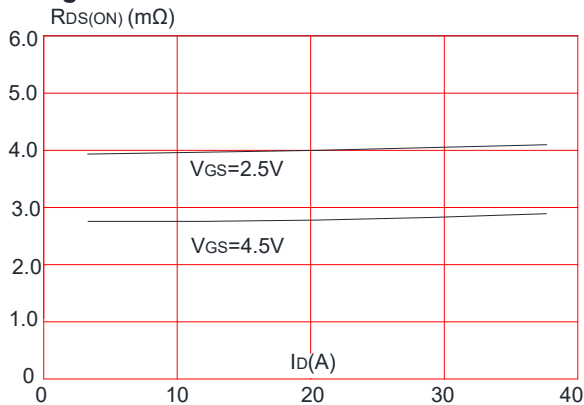


Figure 4: Body Diode Characteristics

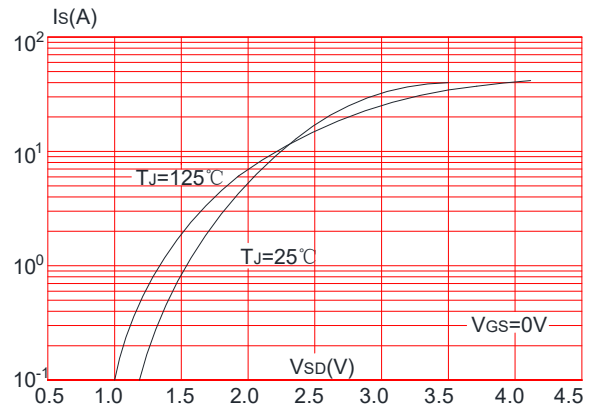


Figure 5: Gate Charge Characteristics

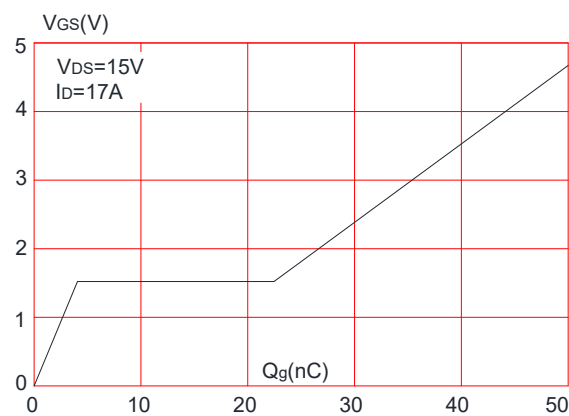


Figure 6: Capacitance Characteristics

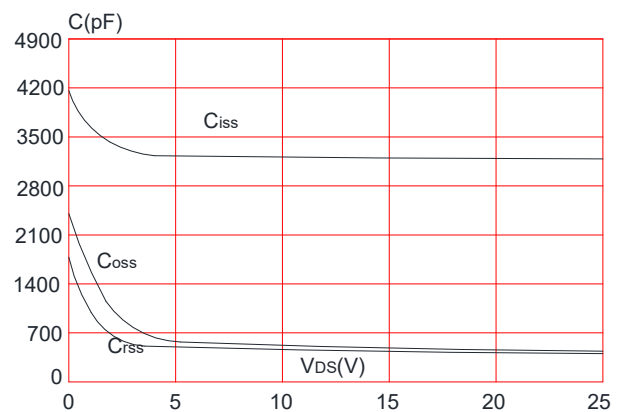


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

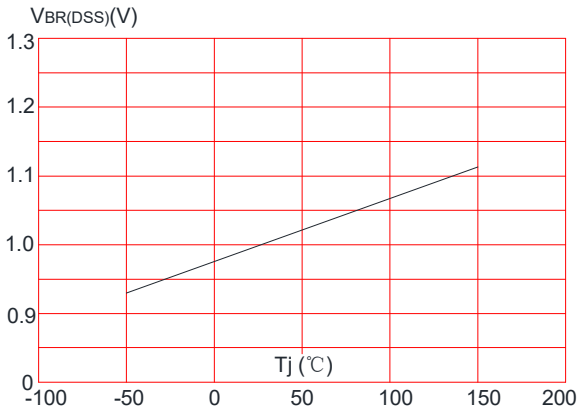


Figure 8: Normalized on Resistance vs. Junction Temperature

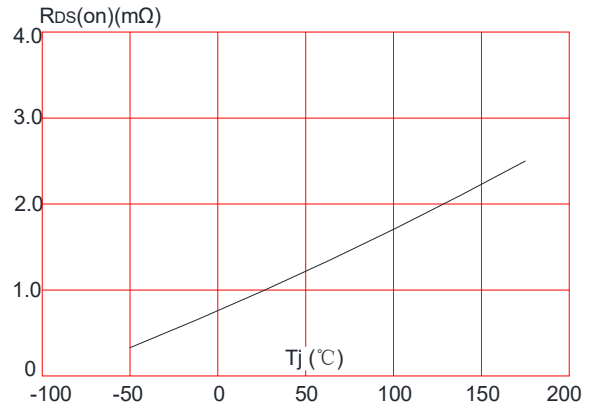


Figure 9: Maximum Safe Operating Area

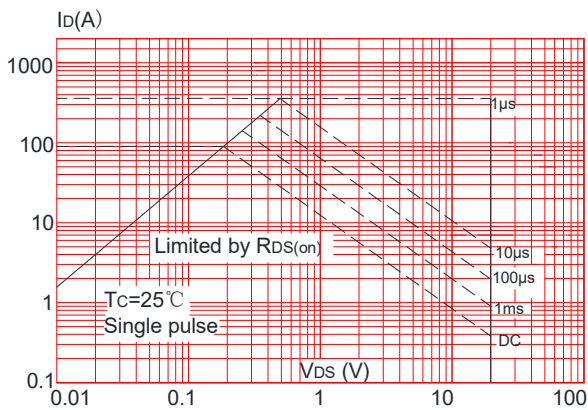


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

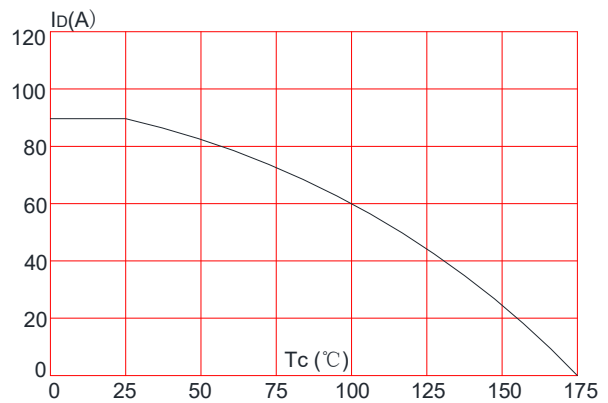
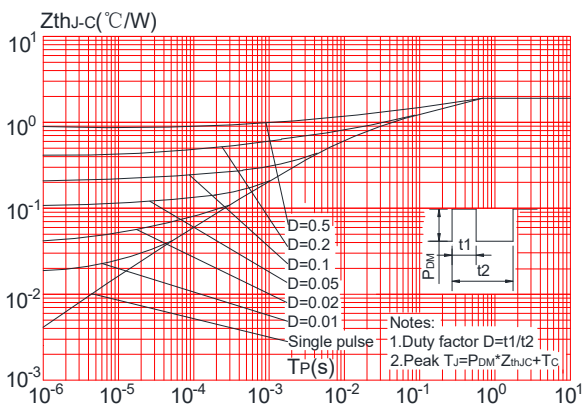


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



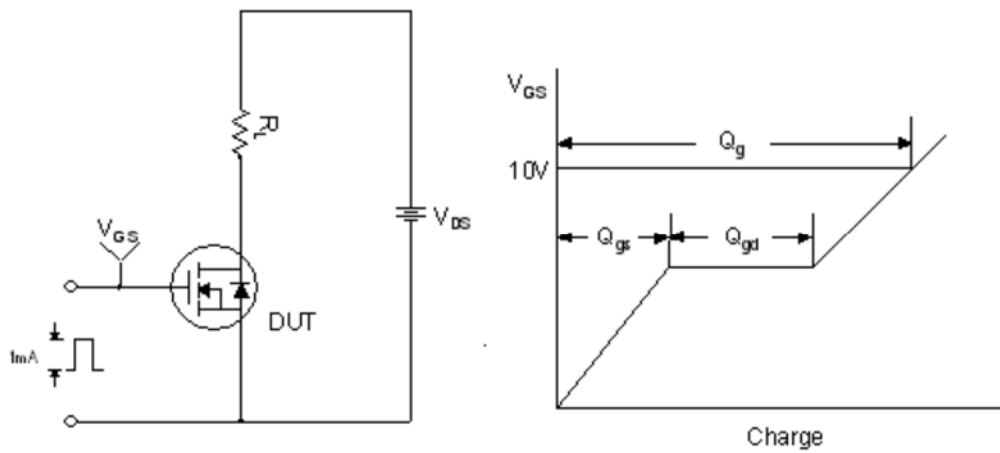


Figure 1. Gate Charge Test Circuit & Waveform

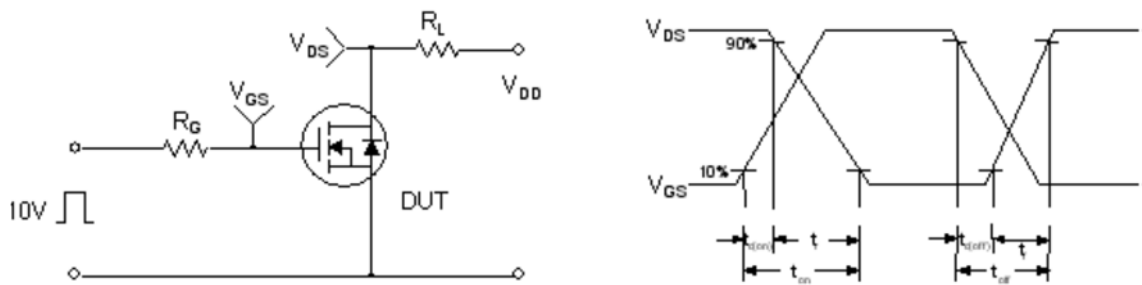


Figure 2. Resistive Switching Test Circuit & Waveforms

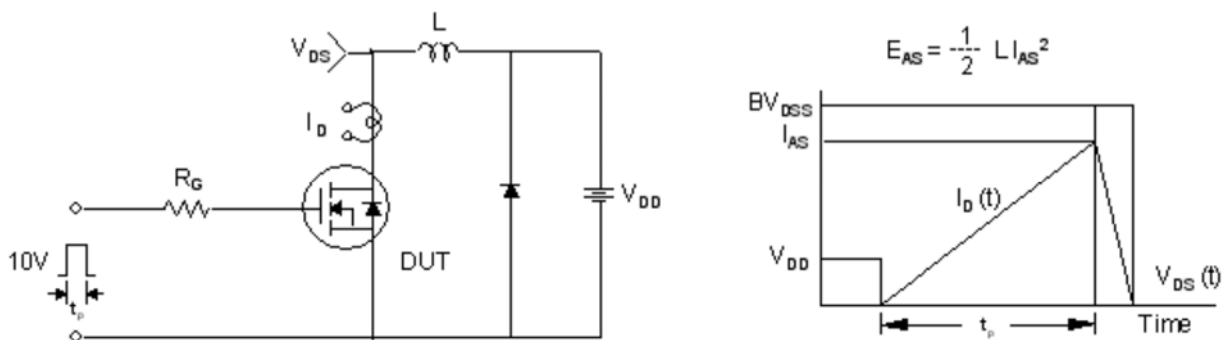
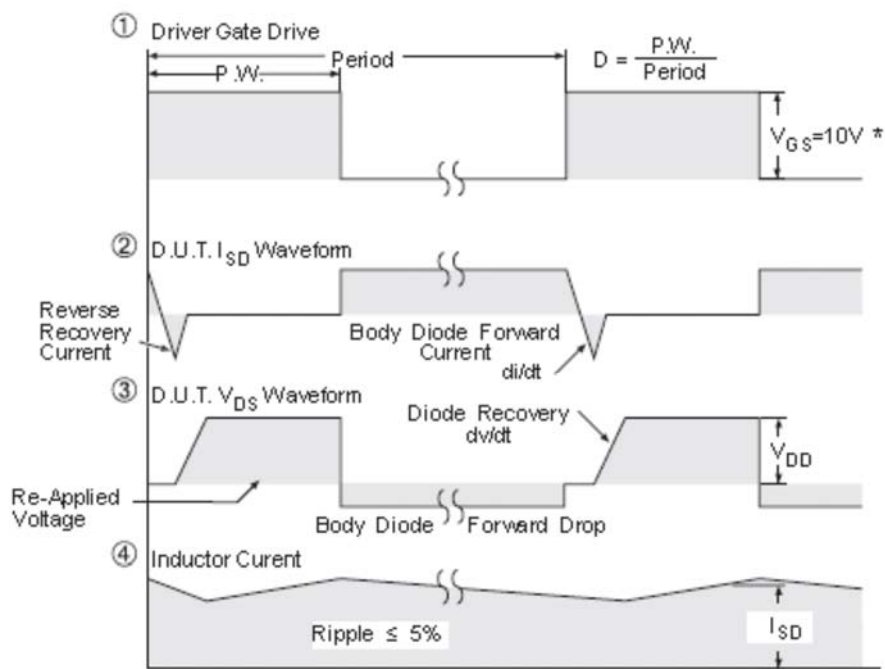
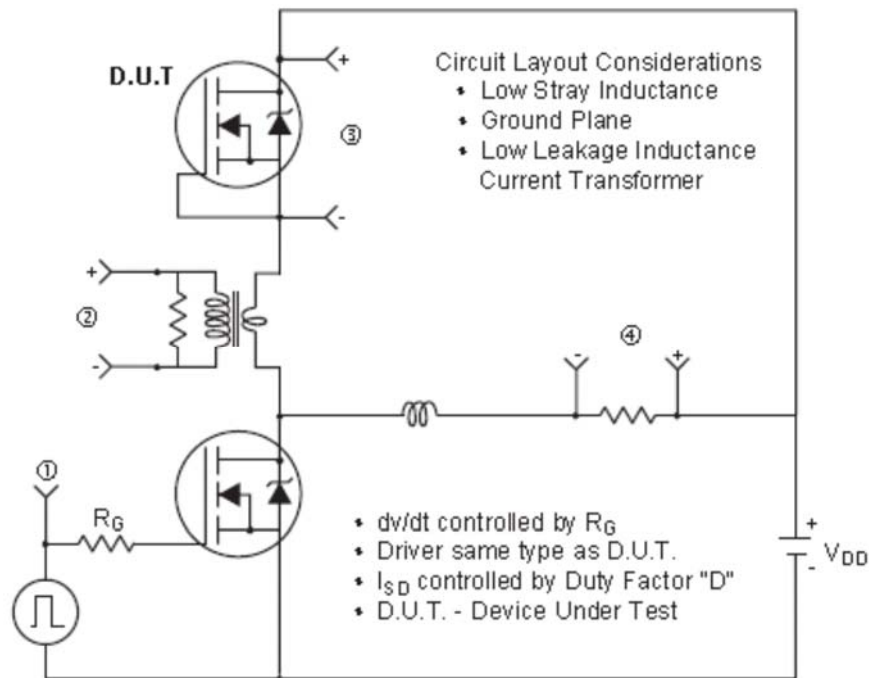


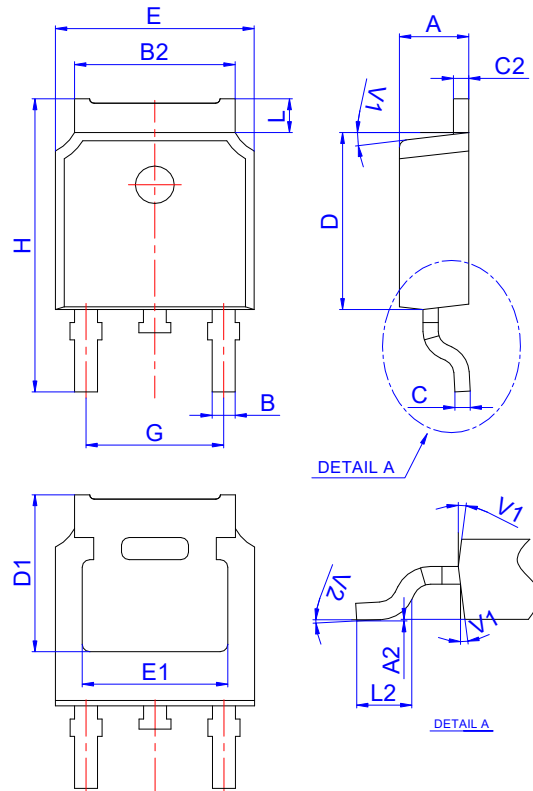
Figure 3. Unclamped Inductive Switching Test Circuit & Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

Figure 4. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

TO-252 PACKAGE OUTLINE DRAWING



Symbols	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°